

8. INDUSTRIAL APPLICATIONS FETs

(1) CHOPPER SWITCHING APPLICATIONS

» JUNCTION FET «

Type No.	V _{GDS} (V)		I _G (mA)	P _D (mW)	T _J (°C)	I _{DSS} *		Main Electrical Characteristics		PACKAGE
	N-Channel	P-Channel				(mA)	V _{DS} (V)			
2SK11	-20		10	100	150	0.3~6.5	10	I _{Yfs1} =0.7~3.2mS @V _{DS} =10V, V _{DS} =0, f=1KHz		TO-17
2SK12	-20		10	100	150	0.45~5.0	10	I _{Yfs1} =0.8~3.2mS @V _{DS} =10V, V _{GS} =0, f=1KHz		TO-17
2SK15	-20		10	100	150	0.45~5.0	10	N _F =3dBMAX. @V _{DS} =10V, I _D =0.45mA, R _g =10kΩ, f=1KHz		TO-17
2SK112	-50		10	250	150	1.2~9.0	15	N _F =2dBMAX. @V _{DS} =15V, I _D =1mA, R _g =1KΩ, f=1KHz		TO-18
2SK113-R	-50		10	250	150	(Note) 5~30	20	R _{ON} =100ΩMAX. @V _{GS} =0, I _D =1mA		TO-18
2SK113-O	-50		10	250	150	(Note) 25~75	20	R _{ON} =60ΩMAX. @V _{GS} =0, I _D =1mA		TO-18
2SK113-Y	-50		10	150	150	(Note)50~150	20	R _{ON} =30ΩMAX. @V _{GS} =0, I _D =1mA		TO-18

* I_{DSS} Classified. (Note) Pulsed

Application

- General Purpose
- Low Noise
- Low Noise
- High I_{Yfs1} Low Noise
- Controlled Resistor
- Switching, Chopper
- Analog Switch, Chopper

» MOS FET «

Type No.	V _{DSS} (V)		V _{G2SS} (V)	V _{G2SS} (V)	I _D (mA)	P _D (mW)	T _{ch} (°C)	R _{ON} (Ω)	CG1S			CG1D (PF)	ΔCG [CA1D,CG1S] (PF)	PACKAGE
	N-CHANNEL	P-CHANNEL							V _{G1S} (V)	V _{G2S} (V)	V _{DS} (mV)			
3SK 38A	20		±12	-20	10	200	125	500 MAX.	3	0	10	2.5 MAX	0.3 MAX.	(2-8E1A)

(Lead: Cu)

Application

- Switching chopper

